



20V NPN LOW SATURATION TRANSISTOR IN U-DFN2020-3

Features

- BVcEo > 20V
- hfe Specified up to 6A for High Current Gain Hold Up
- Low Profile 0.6mm High Package for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: U-DFN2020-3 (Type B)
- Nominal Package Height: 0.6mm
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @4)
- Weight: 0.01 grams (Approximate)

Applications

- DC-DC Converters
- Charging Circuits
- Motor Control
- Power Switches

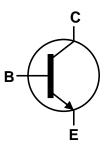
U-DFN2020-3 (Type B)



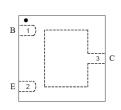




Bottom View



Device Symbol



Top View Pin-Out

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTN5820DFDB-7	2E1	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



2E1= Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2019		2020	2021		2022	2023		2024	2025		2026
Code	G		Н			J	K		L	М		N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	Vcво	20	
Collector-Emitter Voltage	Vceo	20	V
Emitter-Base Voltage	VEBO	6	
Peak Pulse Current	Ісм	8	Α
Continuous Collector Current	Ic	6	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	0-	0.69	W	
Power Dissipation	(Note 6)		1.25	7 vv	
Thermal Resistance, Junction to Ambient	(Note 5)	180		°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	100	C/VV	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

ESD Ratings (Note 7)

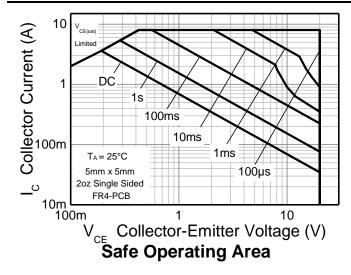
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

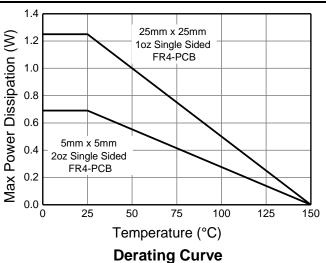
Notes:

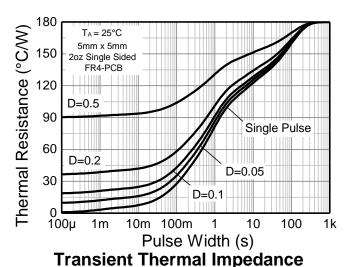
^{5.} For a device mounted with the exposed collector on 5mm x 5mm 2oz copper on single sided FR4 PCB; device is measured under still air conditions whilst operating in the steady state.
6. Same as Note (5) except the exposed collector pad is mounted on 25mm x 25mm 1oz copper.
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

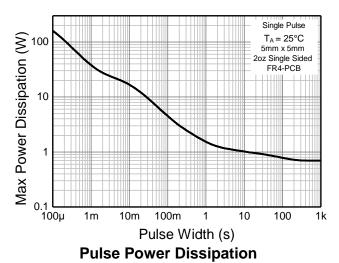


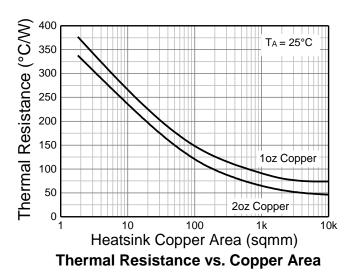
Thermal Characteristics and Derating Information

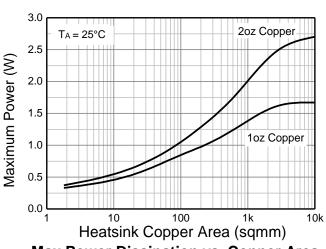












Max Power Dissipation vs. Copper Area



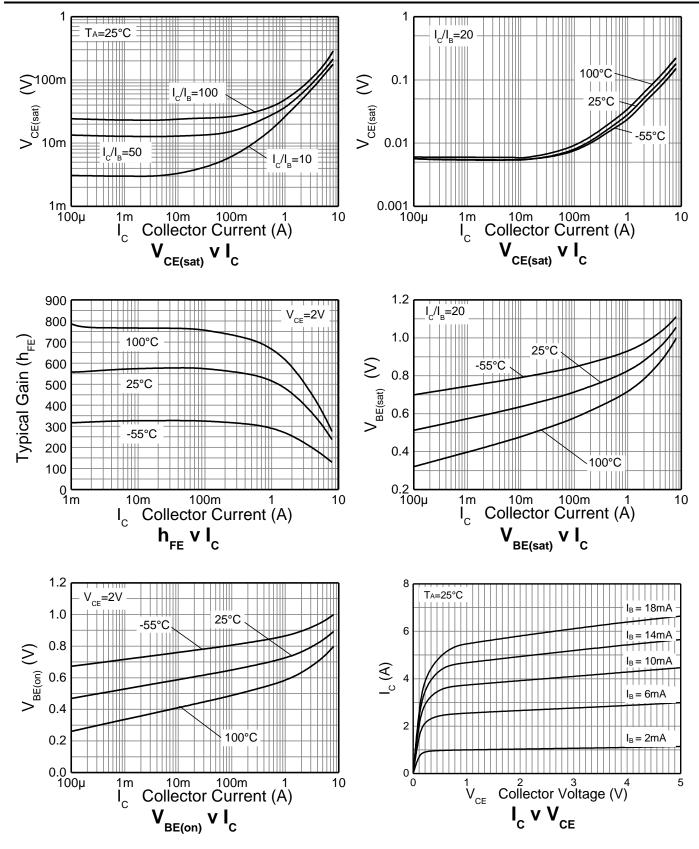
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	ВУсво	20	_		V	Ic = 100μA
Collector-Emitter Breakdown Voltage (Note 8)	BVceo	20	_	_	V	Ic = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	_	V	I _E = 100μA
Collector Cutoff Current	Ісво	_	_	100	nA	V _{CB} = 20V
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	V _{EB} = 5V
Collector Emitter Cutoff Current	Ices	_	_	100	nA	Vces = 16V
		280	530	_		$I_C = 500 \text{mA}, V_{CE} = 2V$
Static Forward Current Transfer Ratio (Note 8)	h	270	500			Ic = 1A, VcE = 2V
Static Forward Current Transfer Ratio (Note 6)	hfE	260	440	_	_	Ic = 2A, VcE = 2V
		180	300	_		$I_C = 6A$, $V_{CE} = 2V$
		_	20	30		$I_C = 0.5A$, $I_B = 50mA$
		_	37	55	mV	Ic = 1A, I _B = 50mA
	VCE(sat)	_	50	70		Ic = 1A, I _B = 10mA
Collector-Emitter Saturation Voltage (Note 8)		_	85	120		Ic = 2A, I _B = 20mA
		_	120	170		$I_C = 3A$, $I_B = 30mA$
		_	135	185		$I_C = 4A$, $I_B = 400mA$
		_	200	275		$I_C = 6A$, $I_B = 300mA$
Base-Emitter Turn-On Voltage (Note 8)	V _{BE(on)}	_	0.74	0.9	V	Ic = 2A, VcE = 2V
Base-Emitter Saturation Voltage (Note 8)	1/		0.75	0.9	V	Ic = 1A, I _B = 10mA
base-Emilier Saluration voltage (Note 6)	V _{BE} (sat)		0.97	1.1		Ic = 6A, I _B = 300mA
Output Capacitance	Cobo	_	80	95	pF	V _{CB} = 10V, f = 1MHz
Transition Frequency	fΤ	_	80	_	MHz	V _{CE} = 10V, I _C = 100mA, f = 100MHz
Delay Time	t _d	_	25	_		
Rise Time	tr	_	55	_		
Turn-On Time	ton	_	80	_		Vcc = 9V, Ic = 2A
Storage Time	ts	_	285	_	ns	I _{B1} = -I _{B2} = 0.1A
Fall Time	t _f	_	50	_		
Turn-Off Time	t _{off}	_	335			

Note: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

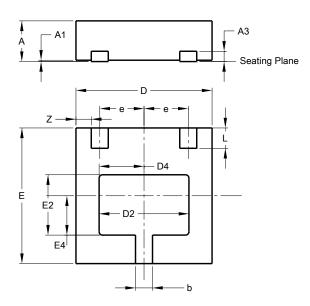




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-3 (Type B)

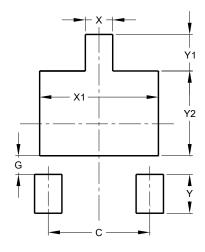


U-DFN2020-3 (Type B)						
Dim	Min	Max	Тур			
Α	0.57	0.63	0.60			
A1	0.00	0.05	0.02			
А3	_		0.152			
b	0.20	0.30	0.25			
D	1.950	2.075	2.00			
D2	1.22	1.42	1.32			
D4	0.56	0.76	0.66			
Е	1.950	2.075	2.00			
E2	0.79	0.99	0.89			
E4	0.48	0.68	0.58			
е	_		0.65			
L	0.25	0.35	0.30			
Z	_	_	0.225			
All Dimensions in mm						

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

U-DFN2020-3 (Type B)



Dimensions	Value (in mm)
С	1.300
G	0.240
Х	0.350
X1	1.520
Υ	0.500
Y1	0.470
Y2	1 090



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